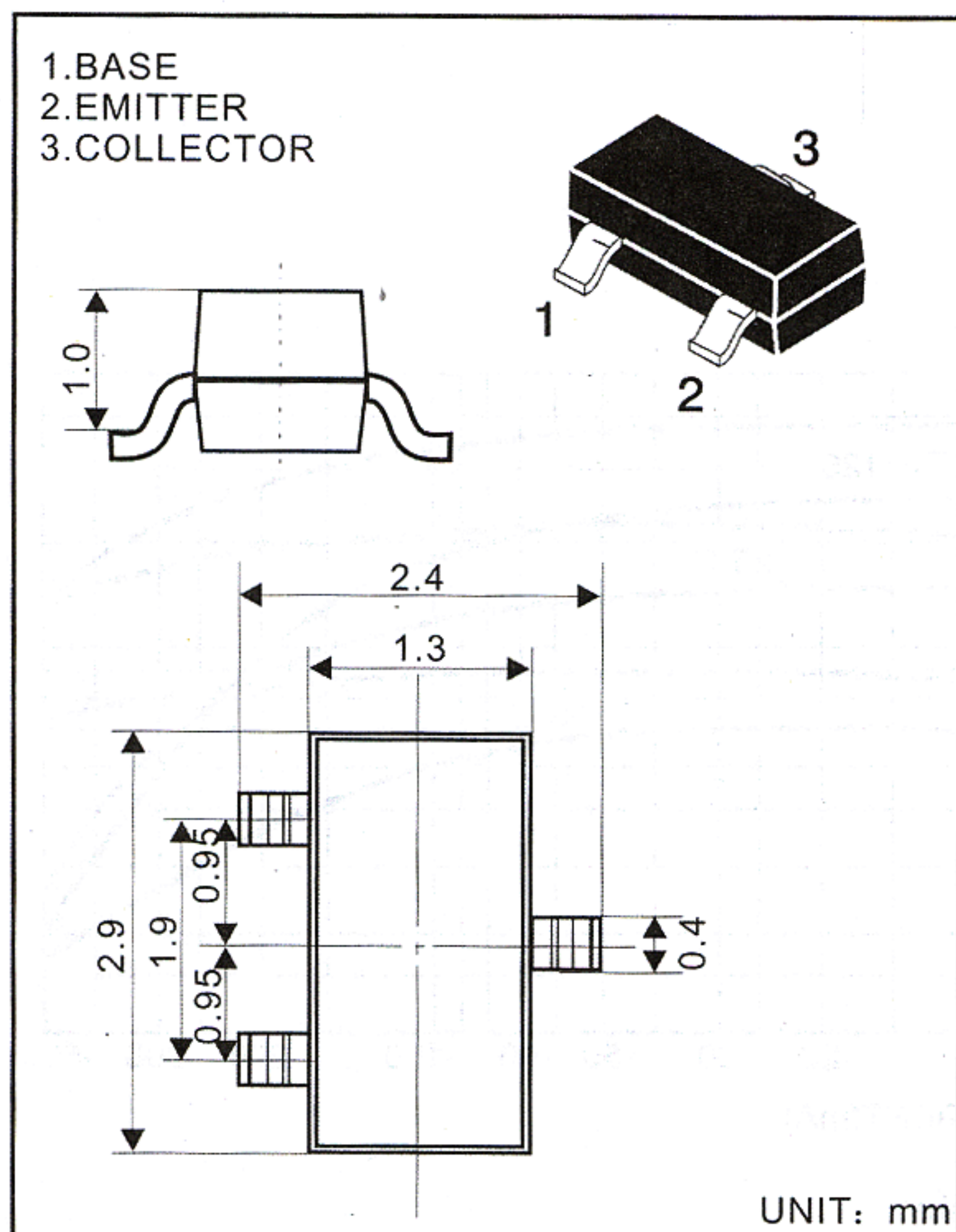


MMBT2907LT1 TRANSISTOR (PNP)



FEATURES

Power dissipation

PCM: 0.3 W (Tamb=25°C)

Collector current

ICM: -0.6 A

Collector-base voltage

V(BR)CBO:-60V

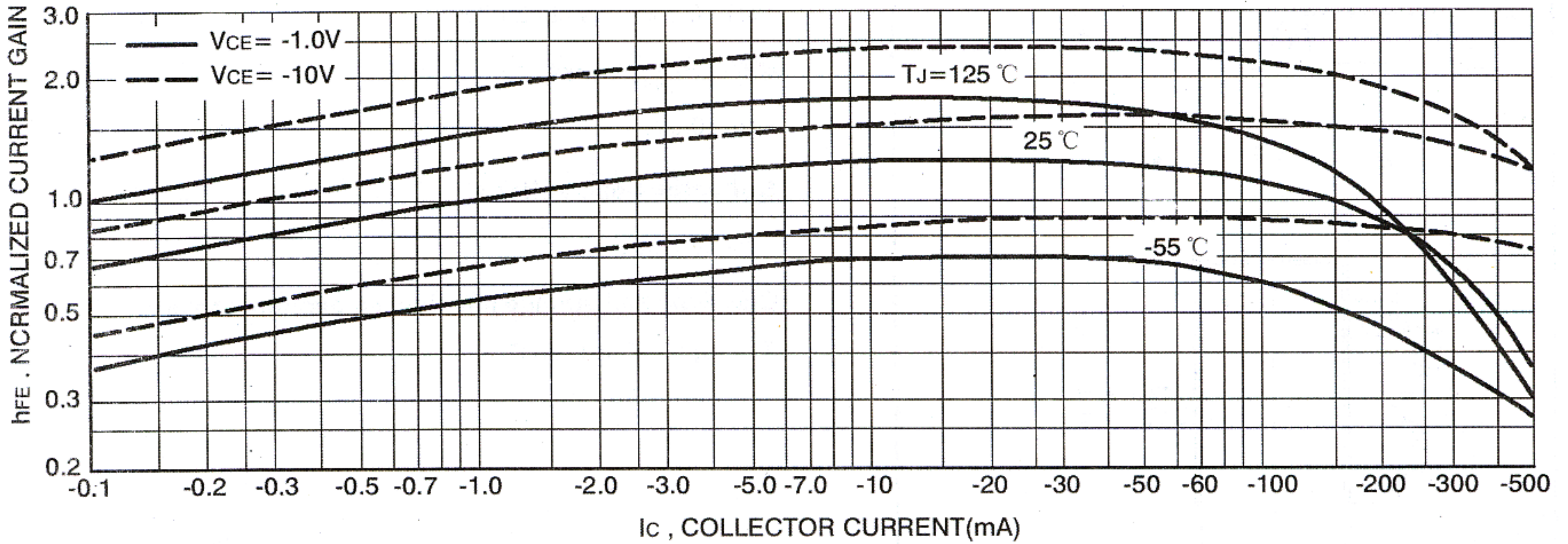
Operating and storage junction temperature range

TJ,Tstg :-55°C to+150°C

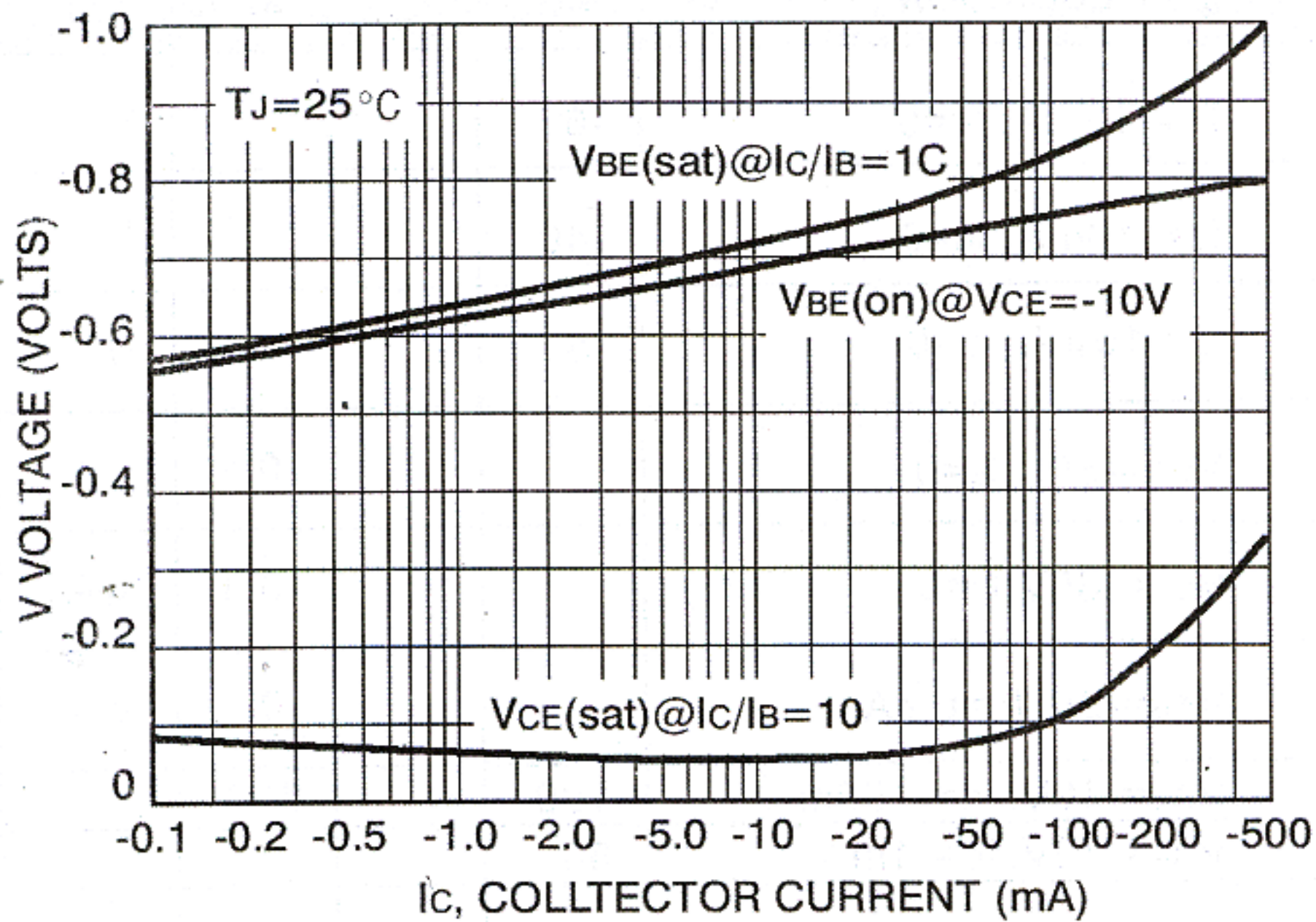
ELECTRICAL CHARACTERISTICS

(Tamp=25°C unless otherwise specified)

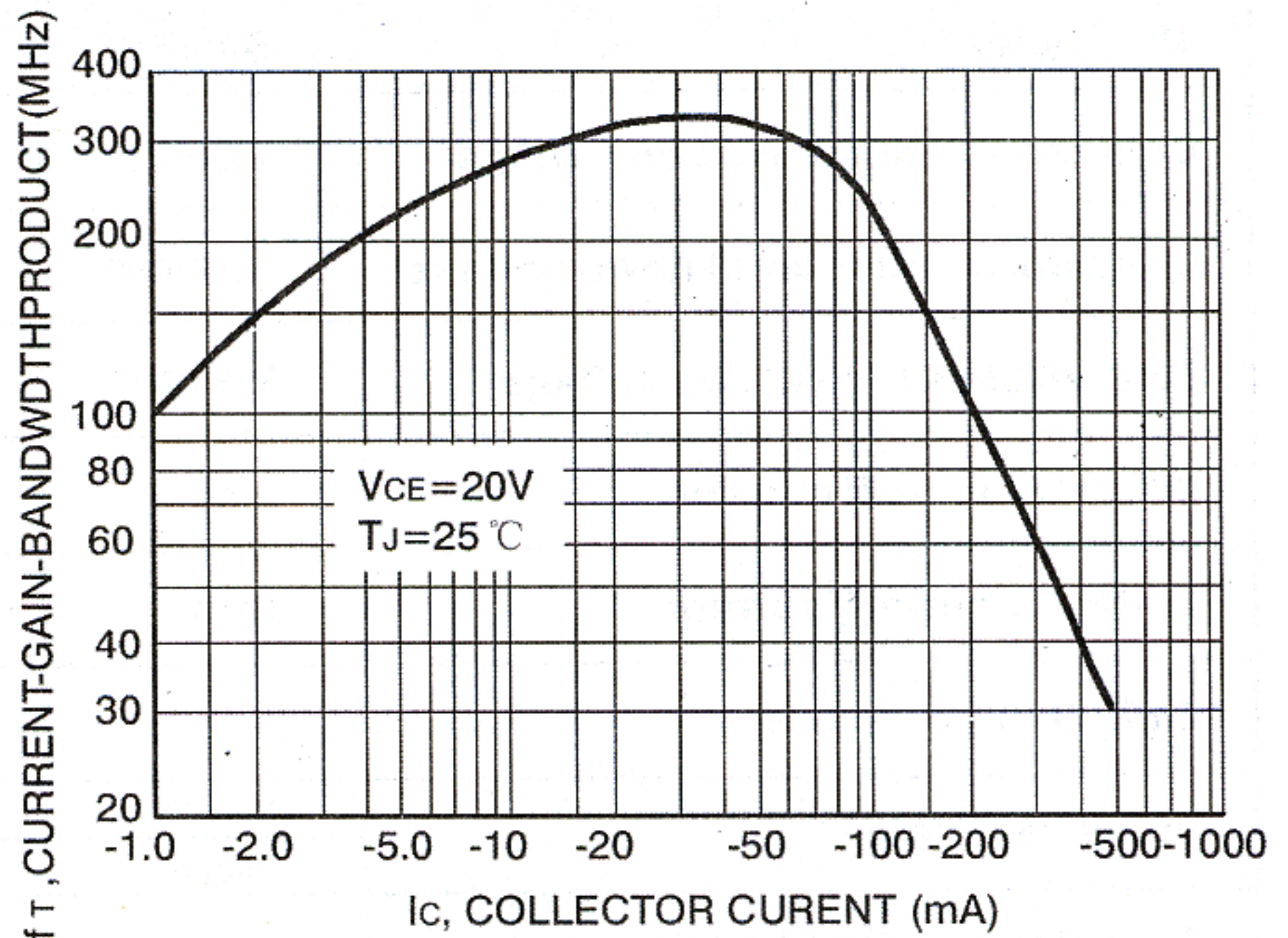
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC=-10 μA, IE=0	-60			V
Collector-emitter breakdown voltage	V(BR)CEO	IC=-10mA, IB=0	-40			V
Emitter-base breakdown voltage	V(BR)EBO	IE=-10 μA, IB=0	-5			V
Collector cut-off current	ICBO	VCB=-50V, IE=0			-0.1	μA
Collector cut-off current	ICEO	VCE=-35V, IB=0			-0.1	μA
Emitter cut-off current	IEBO	VEB=-3V, IC=0mA			-0.1	μA
DC current gain	hFE(1)	VCE=-10V, IC=-150mA	100		300	
	hFE(2)	VCE=-10V, IC=-1mA	50			
Collector-emitter saturation voltage	VCEsat	IC=-500mA, IB=-50mA			-1	V
Base-emitter saturation voltage	VBEsat	IC=-500mA, IB=-50mA			-2	V
Transition frequency	fT	VCE=-20V, IC=-50mA, f=100MHz	200			MHz



DC Current Gain



"On" Voltage



Current-Gain --Bandwidth Product